



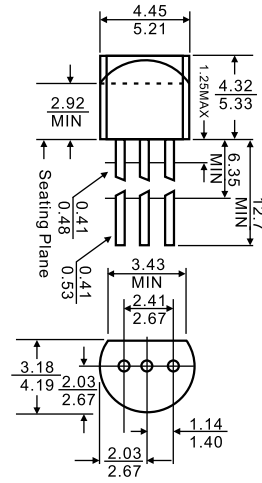
1. EMITTER
2. BASE
3. COLLECTOR

GENERAL PURPOSE APPLICATIONS.
DARLINGTON TRANSISTOR.

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	30	V
Collector-Emitter Voltage	V _{CES}	30	V
Emitter-Base Voltage	V _{EBO}	10	V
Collector Current	I _C	500	mA
Collector Power Dissipation	P _C	625	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C

TO-92

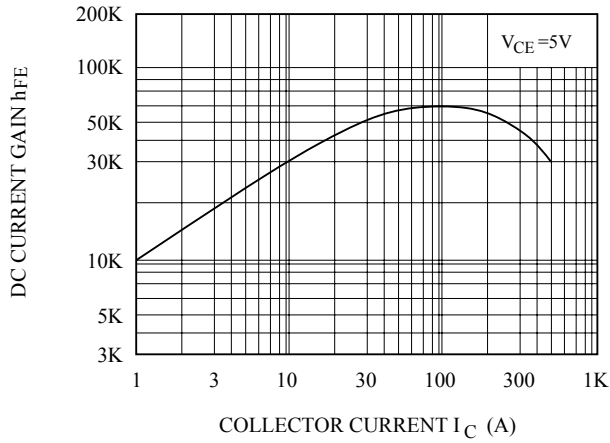


Dimensions in inches and (millimeters)

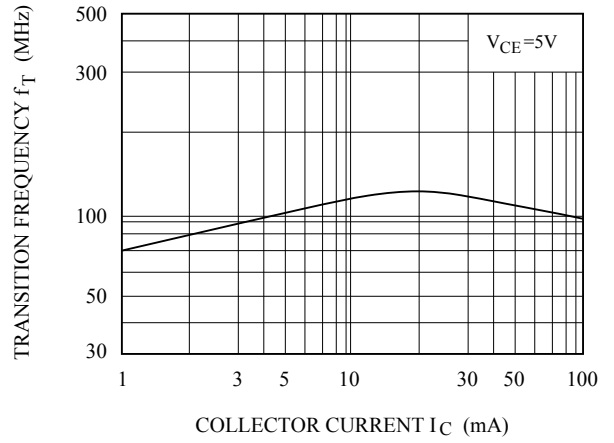
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector-Emitter Breakdown Voltage	V _{CES}	I _C =0.1mA	30	-	-	V	
Emitter Cut-off Current	I _{CBO}	V _{CB} =30V	-	-	100	nA	
Emitter Cut-off Current	I _{EBO}	V _{EB} =10V	-	-	100	nA	
DC Current Gain	MPSA13	I _C =10mA, V _{CE} =5V	5,000	-	-	-	
	MPSA14		10,000	-	-		
	MPSA13		I _C =100mA, V _{CE} =5V	10,000	-		-
	MPSA14			20,000	-		-
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =100mA, I _B =0.1mA	-	-	1.5	V	
Base-Emitter Voltage	V _{BE}	I _C =100mA, V _{CE} =5V	-	-	2.0	V	
Current Gain Bandwidth Product	f _T	I _C =10mA, f=100MHz, V _{CE} =5V	125	-	-	MHz	

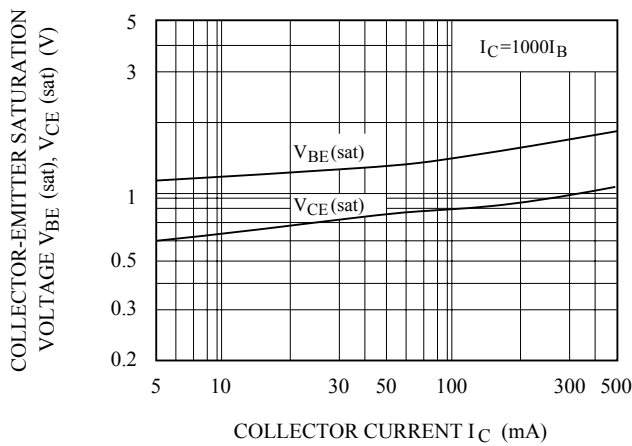
$h_{FE} - I_C$



$f_T - I_C$



$V_{BE}(sat), V_{CE}(sat) - I_C$



$I_C - V_{BE}$

